



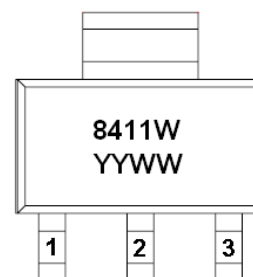
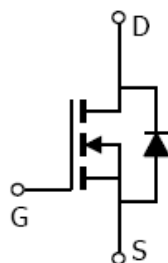
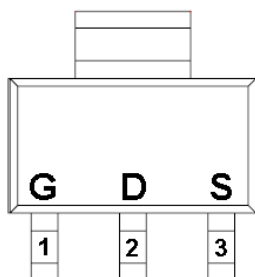
### General Description

AFN8411W, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent  $R_{DS(ON)}$ , low gate charge. These devices are particularly suited for low voltage power management, and low in-line power loss are needed in commercial industrial surface mount applications.

### Features

- 100V/5.8A,  $R_{DS(ON)}=125m\Omega@V_{GS}=10V$
- 100V/4.6A,  $R_{DS(ON)}=140m\Omega@V_{GS}=4.5V$
- Super high density cell design for extremely low  $R_{DS(ON)}$
- SOT-223 package design

### Pin Description ( SOT-223 )



### Application

- Motor and Load Control
- Power Management in White LED System
- Push Pull Converter
- LCD TV Inverter & AD/DC Inverter Systems.

### Pin Define

Pin	Symbol	Description
1	G	Gate
2	D	Drain
3	S	Source

### Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN8411WS223RG	8411W	SOT-223	Tape & Reel	2500 EA

- ※ YY year code
- ※ WW week code
- ※ AFN8411WS223RG : 13" Tape & Reel ; Pb- Free ; Halogen -Free



### Absolute Maximum Ratings

(T<sub>A</sub>=25°C Unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DSS</sub>	100	V
Gate –Source Voltage	V <sub>GSS</sub>	±20	V
Continuous Drain Current(T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	5.8
		T <sub>A</sub> =70°C	4.2
Pulsed Drain Current	I <sub>DM</sub>	10	A
Continuous Source Current(Diode Conduction)	I <sub>S</sub>	1.6	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.8
		T <sub>A</sub> =70°C	1.2
Operating Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	120	°C/W

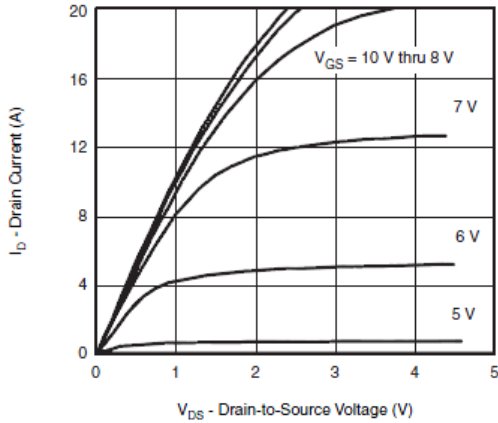
### Electrical Characteristics

(T<sub>A</sub>=25°C Unless otherwise noted)

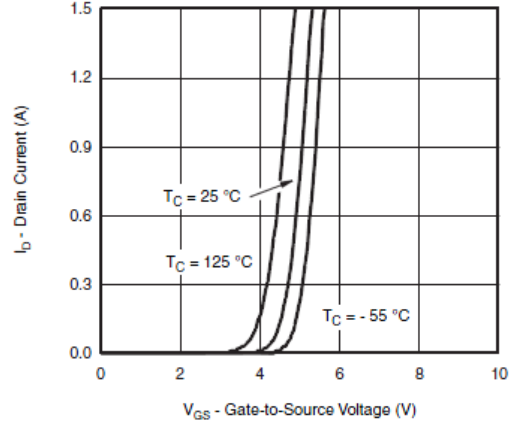
Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	100			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5		2.5	
Gate Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V			±100	nA
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =80V, V <sub>GS</sub> =0V			1	uA
		V <sub>DS</sub> =80V, V <sub>GS</sub> =0V T <sub>J</sub> =85°C			5	
On-State Drain Current	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 5V, V <sub>GS</sub> =4.5V	10			A
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =5.8A		98	125	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =4.6A		128	140	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =5.3A		24		S
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =2.0A, V <sub>GS</sub> =0V		0.8	1.2	V
<b>Dynamic</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =5V I <sub>D</sub> ≡3A		12	18	nC
Gate-Source Charge	Q <sub>gs</sub>			4.2		
Gate-Drain Charge	Q <sub>gd</sub>			5.2		
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V f=1MHz		600		pF
Output Capacitance	C <sub>oss</sub>			90		
Reverse Transfer Capacitance	C <sub>rss</sub>			60		
Turn-On Time	t <sub>d(on)</sub>	V <sub>DD</sub> =50V, R <sub>L</sub> =12.5Ω I <sub>D</sub> ≡3.0A, V <sub>GEN</sub> =10V R <sub>G</sub> =1.0Ω		15	25	ns
	t <sub>r</sub>			15	25	
Turn-Off Time	t <sub>d(off)</sub>			20	30	
	t <sub>f</sub>			15	25	



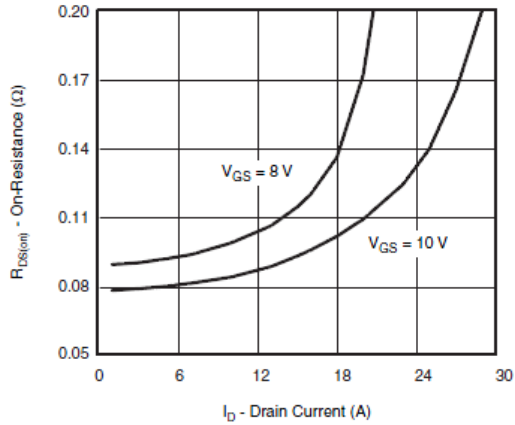
## Typical Characteristics



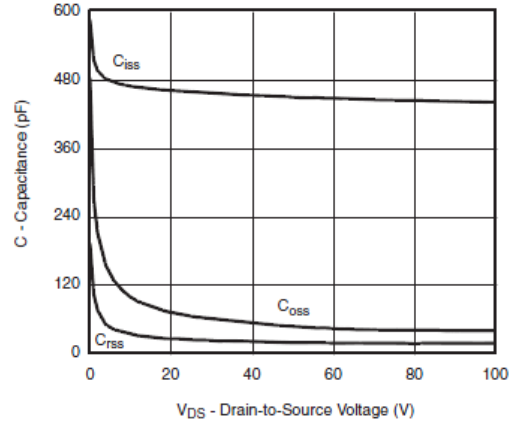
Output Characteristics



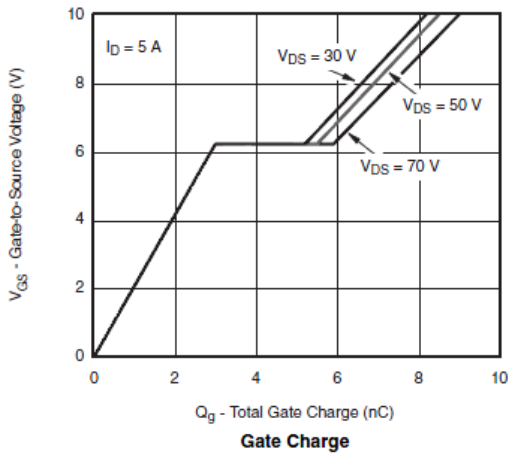
Transfer Characteristics



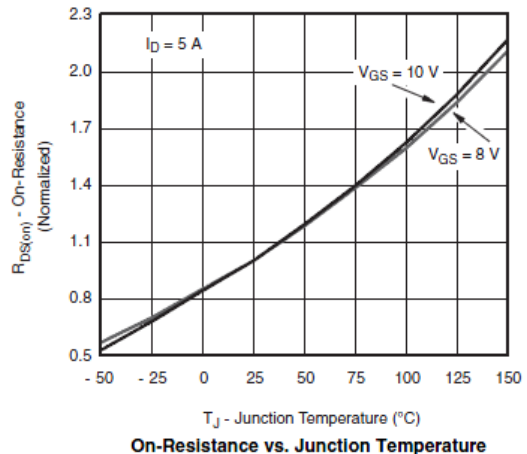
On-Resistance vs. Drain Current and Gate Voltage



Capacitance



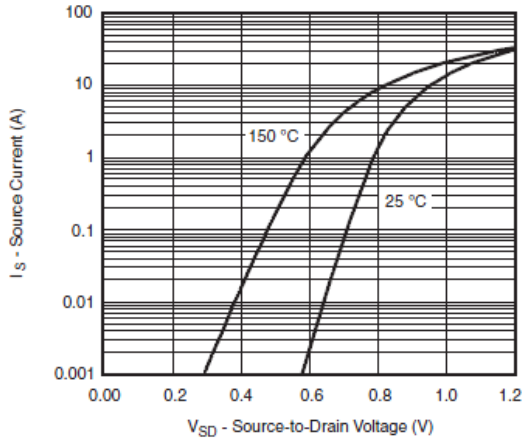
Gate Charge



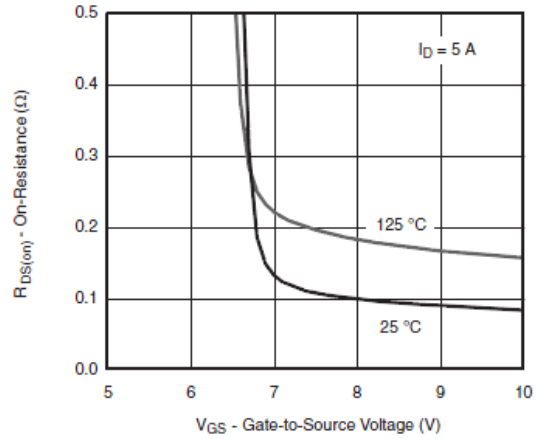
On-Resistance vs. Junction Temperature



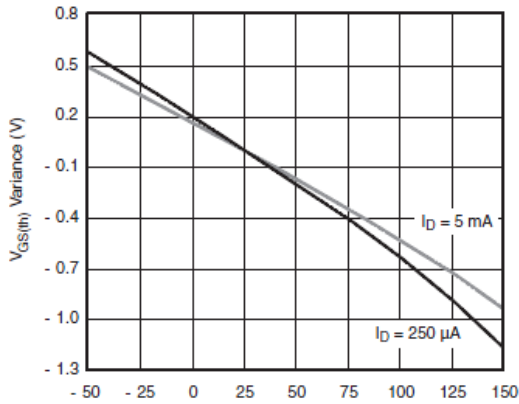
## Typical Characteristics



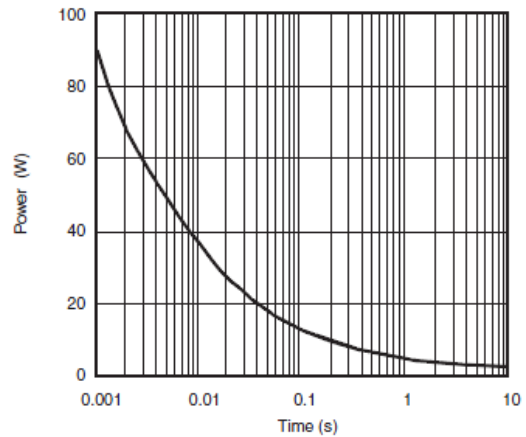
Source-Drain Diode Forward Voltage



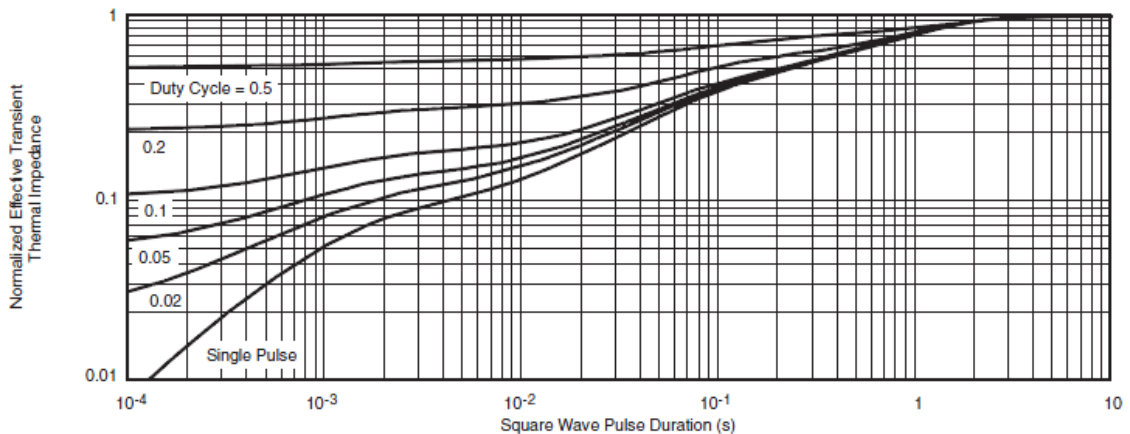
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



Single Pulse Power, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

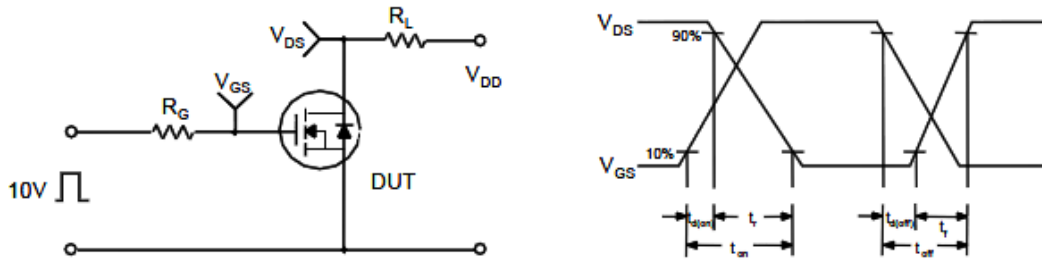


**Typical Characteristics**

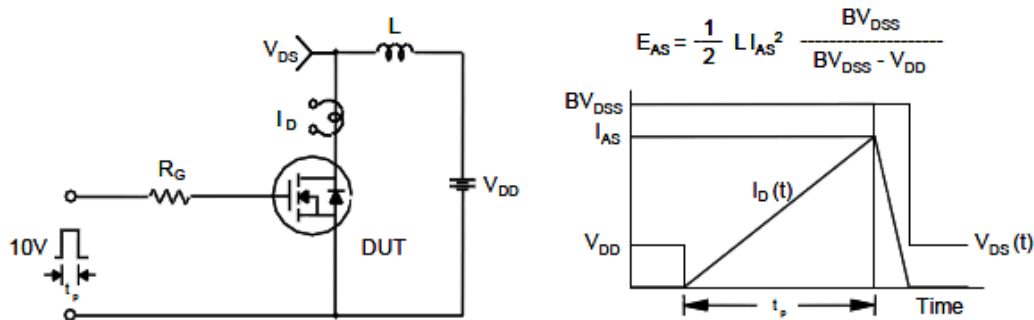
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

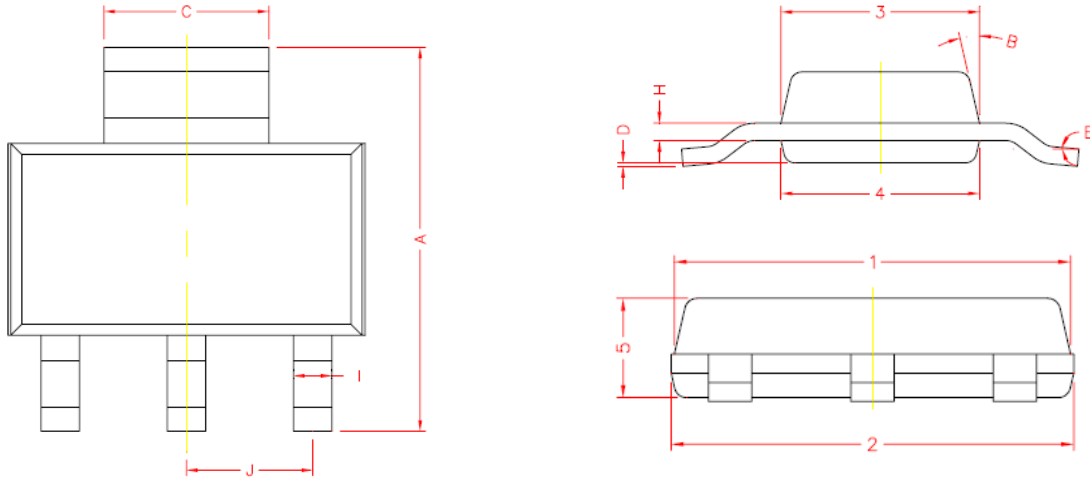


Unclamped Inductive Switching Test Circuit & Waveforms





**Package Information ( SOT-223 )**



REF.	DIMENSIONS	
	Millimeters	
	Min.	Max.
A	6.70	7.30
C	2.90	3.10
D	0.02	0.10
E	0°	10°
I	0.60	0.80
H	0.25	0.35
B	13° TYP.	
J	2.30 REF.	
1	6.30	6.70
2	6.30	6.70
3	3.30	3.70
4	3.30	3.70
5	1.40	1.80

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 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)  
 Tel : 886 2) 2651 3928  
 Fax : 886 2) 2786 8483  
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